



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ko, *et al.* Attorney Docket: TSM02-1383  
Filed: August 27, 2003 Examiner: TBD  
Serial No.: 10/649,566 Art Unit: TBD  
For: Method for Ultra Low-K Dielectric Deposition

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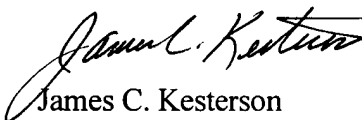
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Respectfully submitted,

  
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Attorney for Applicant  
Reg. No. 25,882

December 2, 2003

Date

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Respectfully submitted,

  
Julie Russell  
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PTO/SB/08A (05-03)

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STATEMENT BY APPLICANT**

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Application Number	10/649,566
Filing Date	August 27, 2003
First Named Inventor	Ko, <i>et al.</i>
Art Unit	TBD
Examiner Name	TBD
Attorney Docket Number	TSM02-1383

Sheet 1 of 2

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
		US-			
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**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
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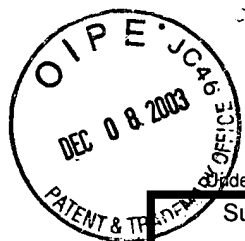
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	A	SHAREEF, I.A., <i>et al.</i> , "Subatmospheric Chemical Vapor Deposition Ozone/TEOS Process for SiO <sub>2</sub> Trench Filling", J. Vac. Sci. Technol. B 13(4), Jul/Aug 1995, pp. 1888-1892, 1995 American Vacuum Society.	
	B	NGUYEN S.V., "High-Density Plasma Chemical Vapor Deposition of Silicon-Based Dielectric Films for Integrated Circuits", IBM Journal of Research and Development, vol. 43, 1/2, 1999.	
	C	IBBOTSON, D.E., <i>et al.</i> , "Plasma Processing of Low K Dielectric Films", The Electrochemical Society, Inc., Washington, D.C., March 25, 2001.	
	D	BEEKMANN, K, <i>et al.</i> , "Low-k Dielectric Requirements and Zero-Overlay Compatibility", Semiconductor International October 21, 2001	
	E	KALLENDER, P., "Toshiba, Fujitsu Report 100-Nanometer Process Gains", EE Times, November 8, 2001	
	F	WALDFRIED, C, <i>et al.</i> , "Plasma Curing of Porous MSQ Films", 202 <sup>nd</sup> ECS Meeting, October 20-25, 2002.	

Examiner Signature		Date Considered	
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	G	LEE, H.J. <i>et al.</i> , "Structural Characterization of Porous Low-k SiOC Thin Films Using X-ray Porosimetry," publication and date unknown.	
	H	"MEMS Thin Film Deposition Processes," MEMS and Nanotechnology Clearinghouse, author and date unknown.	
	I	USAMI, K., <i>et al.</i> , "A Silica-Based Inter-Metal-Insulator with Low Dielectric-Constant and High Thermal Conductivity," publication and date unknown.	

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